



DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
30V	20mΩ @ V _{GS} = 10V	10A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions
- DC-DC Converters
- Analog Switch

Features and Benefits

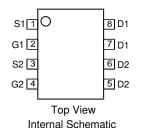
- Low On-Resistance
- Low Input Capacitance
- Low Input/Output Leakage
- Low Gate Resistance
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- An Automotive-Compliant Part is Available Under Separate Datasheet (DMG4822SSDQ)

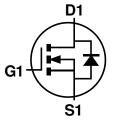
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4
- Weight: 0.072 grams (Approximate)

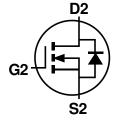


Top View





N-Channel MOSFET



N-Channel MOSFET

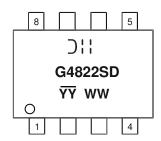
Ordering Information (Note 4)

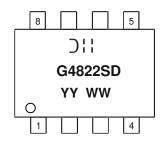
-		
Part Number	Case	Packaging
DMG4822SSD-13	SO-8	2,500/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information





Oll = Manufacturer's Marking G4822SD = Product Type Marking Code YYWW = Date Code Marking YY or YY = Year (ex: 19 = 2019) WW = Week (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +85$ °C	I _D	10 6.6	А
Pulsed Drain Current (Note 6)			I _{DM}	60	Α
Avalanche Current (Notes 7 & 8)			I _{AR}	1.68	Α
Repetitive Avalanche Energy L = 0.3mH (Notes 7 & 8)			E _{AR}	12.8	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	1.42	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	88.4	°C/W
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C

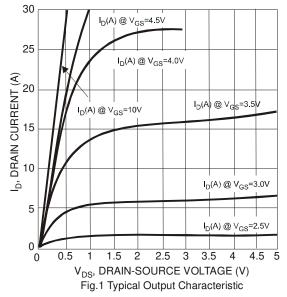
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

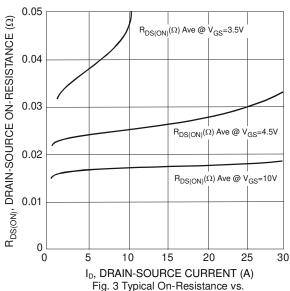
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V$, $I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	l	_	1	μΑ	$V_{DS} = 30V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	l	_	±100	nA	$V_{GS} = \pm 25V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		l	13.4	20	mΩ	$V_{GS} = 10V, I_D = 8.5A$	
Static Dialii-Source Off-Nesistance	R _{DS(ON)}	l	19.5	31	11122	$V_{GS} = 4.5V, I_D = 6A$	
Forward Transfer Admittance	Y _{fs}	l	20	_	mS	$V_{DS} = 5V, I_D = 8.5A$	
Diode Forward Voltage	V_{SD}	_	0.4	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	l	478.9	_	рF	101/1/	
Output Capacitance	Coss	_	96.7	_	рF	$V_{DS} = 16V, V_{GS} = 0V,$ - f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	-	61.4	_	рF	T = TMHZ	
Gate Resistance	R_g	_	1.1	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{g}	-	5	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q_g	l	10.5	_	nC	$V_{GS} = 10V, V_{DS} = 15V,$	
Gate-Source Charge	Q_{gs}	_	1.8	_	nC	$I_D = 8.5A$	
Gate-Drain Charge	Q_{gd}	_	1.6	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	2.9	_	ns		
Turn-On Rise Time	t _R	-	7.9	_	ns	$V_{DS} = 15V, V_{GS} = 10V,$	
Turn-Off Delay Time	t _{D(OFF)}	-	14.6	_	ns	$R_L = 1.8\Omega, R_G = 3\Omega$	
Turn-Off Fall Time	t _F	_	3.1	_	ns		

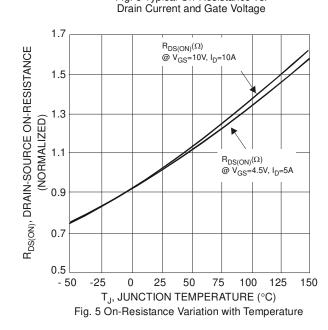
5. Device mounted on FR-4 PCB, with minimum recommended pad layout. Notes:

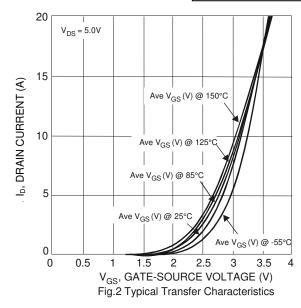
- 6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
 7. Repetitive rating, pulse width limited by junction temperature.
- 8. I_{AR} and E_{AR} ratings are based on low frequency and duty cycles to keep $T_{J} = +25$ °C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.

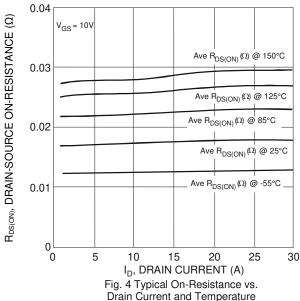


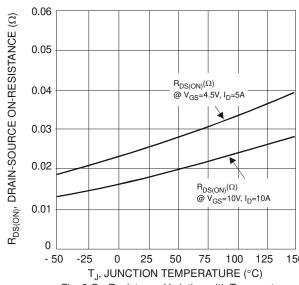














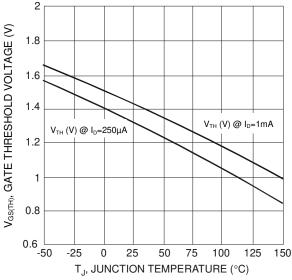


Fig. 7 Gate Threshold Variation vs. Junction Temperature

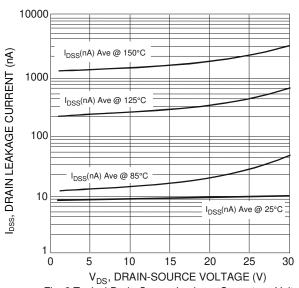
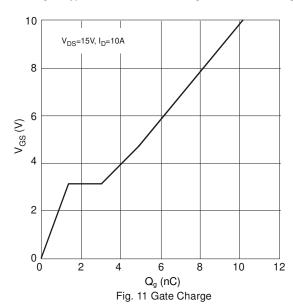
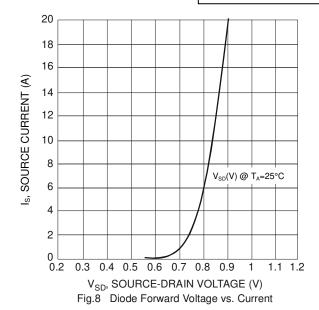
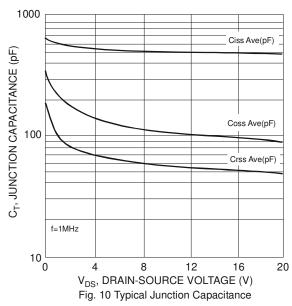
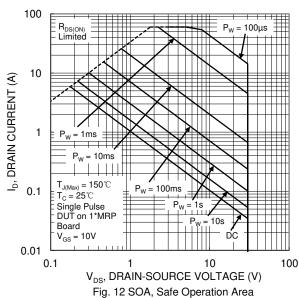


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage











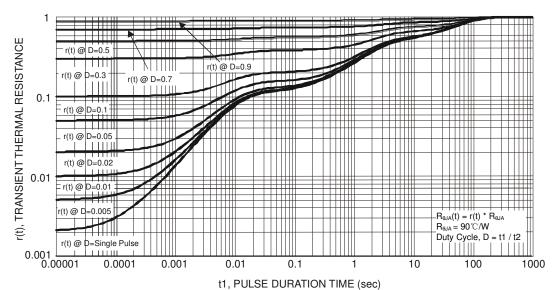


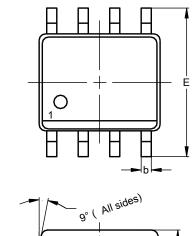
Fig. 13 Transient Thermal Resistance

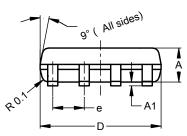


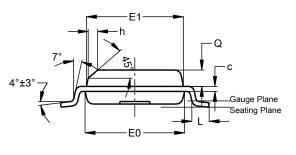
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





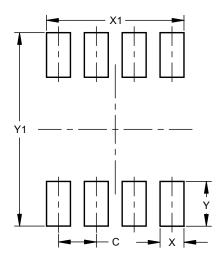


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
٦	0.62	0.82	0.72		
Ø	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8



Dimensions	Value (in mm)
С	1.27
Х	0.802
X1	4.612
Υ	1.505
V1	6.50



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